

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1 (currently amended): A semiconductor light-emitting device comprising:

a semiconductor light-emitting device chip including a chip substrate and a stack formed of semiconductor layers stacked on a surface of said chip substrate; and

a mount member having a mount surface, wherein

said semiconductor light-emitting device chip is connected to the mount surface of said mount member by solder between the semiconductor light-emitting device chip and said mount surface of said mount member, with said stack facing said mount surface ; ~~and~~

said mount member includes a material higher in thermal expansion coefficient than a material for said chip substrate,

said chip substrate includes nitride-based compound semiconductor, and

said stack includes nitride-based compound semiconductor.

Claim 2 (previously presented): A semiconductor light-emitting device comprising:

a semiconductor light-emitting device chip including a chip substrate and a stack formed of semiconductor layers stacked on a surface of said chip substrate; and

a mount member having a mount surface, wherein

said semiconductor light-emitting device chip is connected to the mount surface of said mount member by solder between the semiconductor light-emitting device chip and said mount surface of said mount member, with said stack facing said mount surface,

said mount surface is curved to protrude and said semiconductor light-emitting device chip is curved along and connected to said mount surface, and

said stack includes nitride-based compound semiconductor.

Claim 3 (cancelled)

Claim 4 (previously presented): The semiconductor light-emitting device according to claim 1, wherein

said mount member includes at least one of iron and copper.

Claim 5 (previously presented): The semiconductor light-emitting device according to claim 1, wherein

said mount surface and said stack are connected by solder and said solder includes at least one selected from the group consisting of In, Sn, Pb and Au.

Claim 6 (cancelled)

Claim 7 (previously presented): The semiconductor light-emitting device according to claim 5, wherein

said mount member includes at least one of iron and copper.

Claim 8 (previously presented): The semiconductor light-emitting device according to claim 2, wherein

said chip substrate includes nitride-based compound semiconductor .

Claim 9 (previously presented): The semiconductor light-emitting device according to claim 8, wherein

said mount member includes at least one of iron and copper.

Claim 10 (currently amended): A semiconductor light-emitting device comprising:
a semiconductor light-emitting device chip including a chip substrate and a stack formed of semiconductor layers stacked on a surface of said chip substrate; and
a mount member having a mount surface, wherein
said semiconductor light-emitting device chip is connected to the mount surface of said mount member by solder between the semiconductor light-emitting device chip and said mount surface of said mount member, with said stack facing said mount surface,
said mount member includes a material higher in thermal expansion coefficient than a material for said chip substrate; and
said stack is formed by stacking the semiconductor layers on the surface of said chip substrate in advance of connecting said semiconductor light-emitting device chip to the mount surface of said mount member,
said chip substrate includes nitride-based compound semiconductor, and
said stack includes nitride-based compound semiconductor.

Claim 11 (cancelled)

Claim 12 (previously presented): The semiconductor light-emitting device according to claim 10, wherein
said mount member includes at least one of iron and copper.

Claim 13 (currently amended): A semiconductor light-emitting device comprising:
a semiconductor light-emitting device chip including a chip substrate and a stack formed of semiconductor layers stacked on a surface of said chip substrate; and
a mount member having a mount surface, wherein

said semiconductor light-emitting device chip is connected to the mount surface of said mount member by solder between the semiconductor light-emitting device chip and said mount surface of said mount member, with said stack facing said mount surface,

said mount surface is curved to protrude and said semiconductor light-emitting device chip is curved along and connected to said mount surface, and

said stack is formed by stacking the semiconductor layers on the surface of said chip substrate in advance of connecting said semiconductor light-emitting device chip to the mount surface of said mount member, and

said stack includes nitride-based compound semiconductor.

Claim 14 (previously presented): The semiconductor light-emitting device according to claim 13, wherein

said chip substrate includes nitride-based compound semiconductor.

Claim 15 (previously presented): The semiconductor light-emitting device according to claim 14, wherein

said mount member includes at least one of iron and copper.

Claim 16 (previously presented): A semiconductor light-emitting device comprising:
a semiconductor light-emitting device chip including a chip substrate and a stack formed of semiconductor layers stacked on a surface of said chip substrate; and

a mount member having a mount surface, wherein

said semiconductor light-emitting device chip is connected to the mount surface of said mount member with said stack facing said mount surface,

said mount member includes a material higher in thermal expansion coefficient than a material for said chip substrate,

wherein said mount surface and said stack are connected by solder and said solder includes at least one selected from the group consisting of In, Sn, Pb and Au,

said chip substrate includes nitride-based compound semiconductor, and

said stack includes nitride-based compound semiconductor.

Claim 17 (cancelled)

Claim 18 (previously presented): The semiconductor light-emitting device according to claim 16, wherein

said mount member includes at least one of iron and copper.

Claim 19 (previously presented): The semiconductor light-emitting device according to claim 1, wherein

an electrode is provided on said chip substrate.

Claim 20 (previously presented): The semiconductor light-emitting device according to claim 10, wherein

an electrode is provided on said chip substrate.

Claim 21 (previously presented): The semiconductor light-emitting device according to claim 16, wherein

an electrode is provided on said chip substrate.